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Kind regards,

Team Nexperia

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

Rev. 10 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package	-		NPN	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA114EE	SOT416	SC-75	-	PDTC114EE	ultra small	
PDTA114EM	SOT883	SC-101	-	PDTC114EM	leadless ultra small	
PDTA114ET	SOT23	-	TO-236AB	PDTC114ET	small	
PDTA114EU	SOT323	SC-70	-	PDTC114EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified
- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
l _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	



PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
SOT23; S	OT323; SOT416		
1	input (base)		
2	GND (emitter)	3	
3	output (collector)	12	1 R1 R2 sym003
SOT883			
1	input (base)		
2	GND (emitter)	1 3	
3	output (collector)	2 Transparent top view	1 R1 R2 R2 sym003

3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
PDTA114EE	SC-75	plastic surface-mounted package; 3 leads	SOT416				
PDTA114EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTA114ET	-	plastic surface-mounted package; 3 leads	SOT23				
PDTA114EU	SC-70	plastic surface-mounted package; 3 leads	SOT323				

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PDTA114EE	03
PDTA114EM	E5
PDTA114ET	*03
PDTA114EU	*03

[1] * = placeholder for manufacturing site code.

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

5. Limiting values

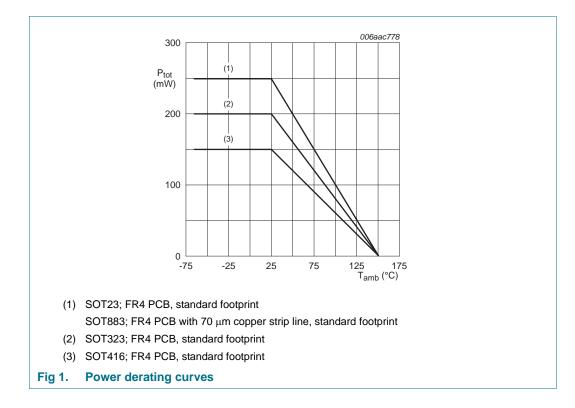
Table 6. In accorda	Limiting values ance with the Absolute Maxim	num Rating System (IEC 60	0134).			
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-10	V
VI	input voltage					
	positive			-	+40	V
	negative			-	-10	V
lo	output current			-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	PDTA114EE (SOT416)		[1][2]	-	150	mW
	PDTA114EM (SOT883)		[2][3]	-	250	mW
	PDTA114ET (SOT23)		<u>[1]</u>	-	250	mW
	PDTA114EU (SOT323)		<u>[1]</u>	-	200	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 µm copper strip line, standard footprint.

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω



6. Thermal characteristics

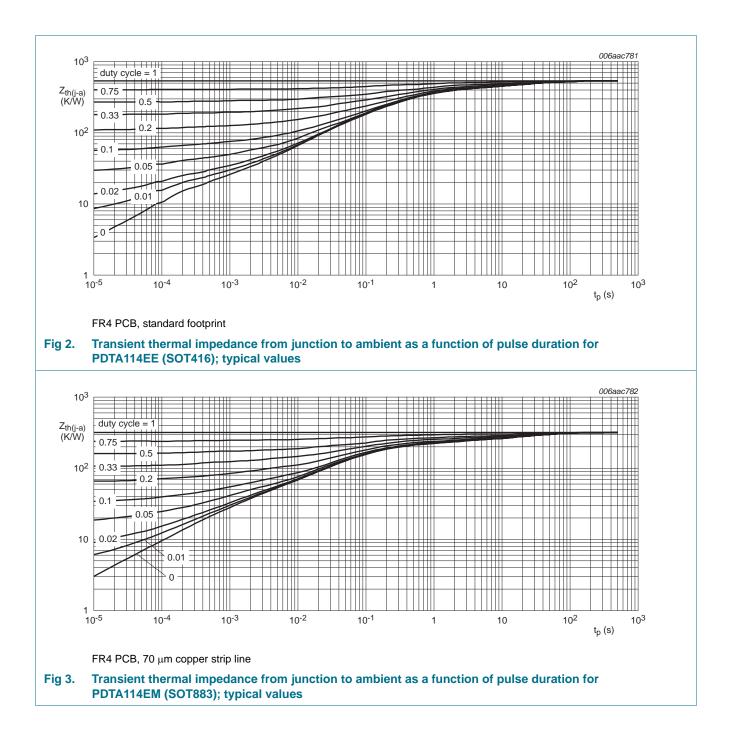
Table 7.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air					
	PDTA114EE (SOT416)		[1][2]	-	-	830	K/W
	PDTA114EM (SOT883)		[2][3]	-	-	500	K/W
	PDTA114ET (SOT23)		<u>[1]</u> .	-	-	500	K/W
	PDTA114EU (SOT323)		<u>[1]</u> .	-	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

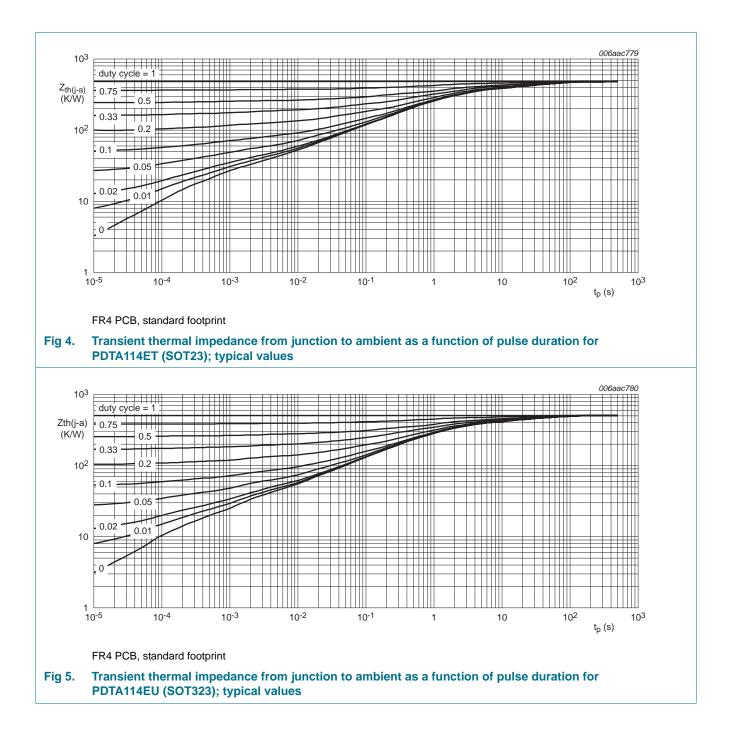
[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 70 μ m copper strip line, standard footprint.

PDTA114E series



PDTA114E series



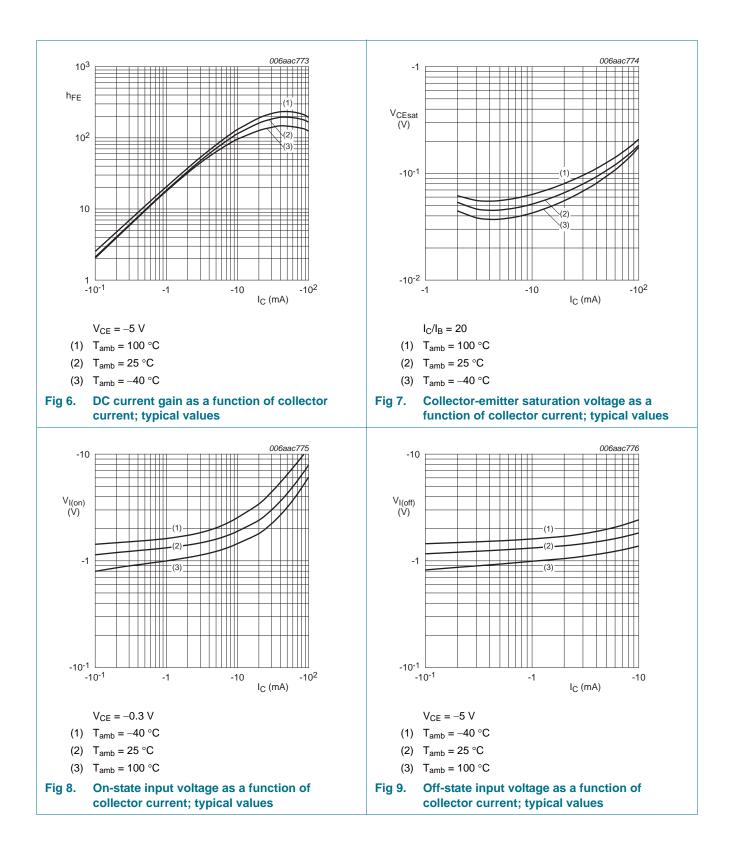
PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

7. Characteristics

Table 8. $T_{amb} = 25$	Characteristics ℃ unless otherwise sp	ecified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	V_{CE} = –30 V; I_{B} = 0 A	-	-	-1	μΑ
	cut-off current	$\label{eq:Vce} \begin{array}{l} V_{CE} = -30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-400	μΑ
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -5 mA	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -10 \text{ mA};$ $I_{\rm B} = -0.5 \text{ mA}$	-	-	-150	mV
V _{I(off)}	off-state input voltage	$V_{CE} = -5 V;$ $I_{C} = -100 \ \mu A$	-	-1.1	-0.8	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 V;$ $I_{C} = -10 mA$	-2.5	-1.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \ V; \\ I_{E} = i_{e} = 0 \ A; \ f = 1 \ MHz \end{array}$	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 V;$ $I_{C} = -10 mA;$ f = 100 MHz	<u>[1]</u> -	180	-	MHz

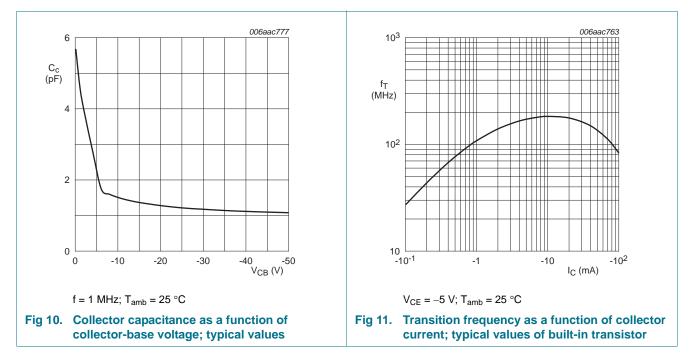
[1] Characteristics of built-in transistor.

PDTA114E series



PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω



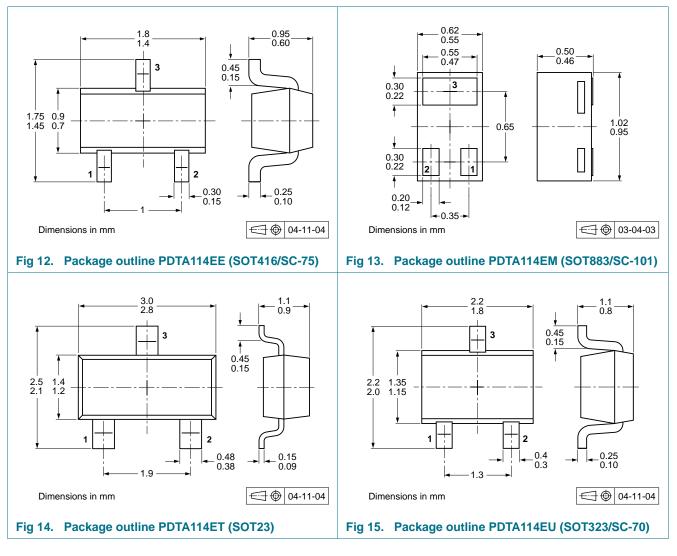
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

9. Package outline



10. Packing information

Table 9. Packing methods

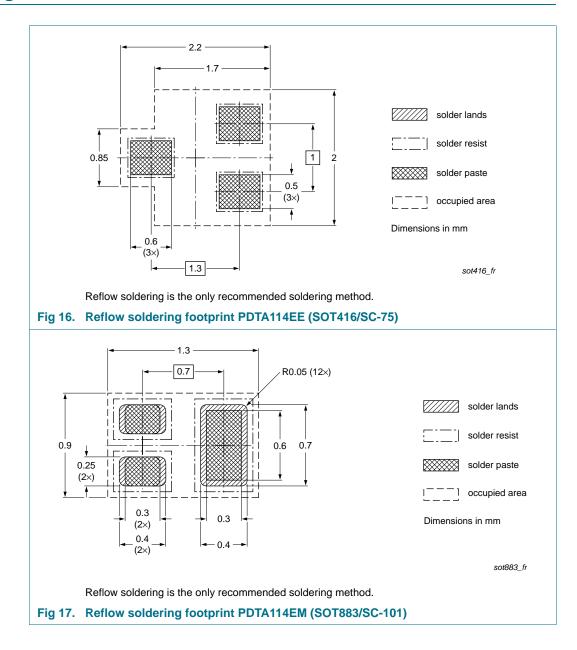
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

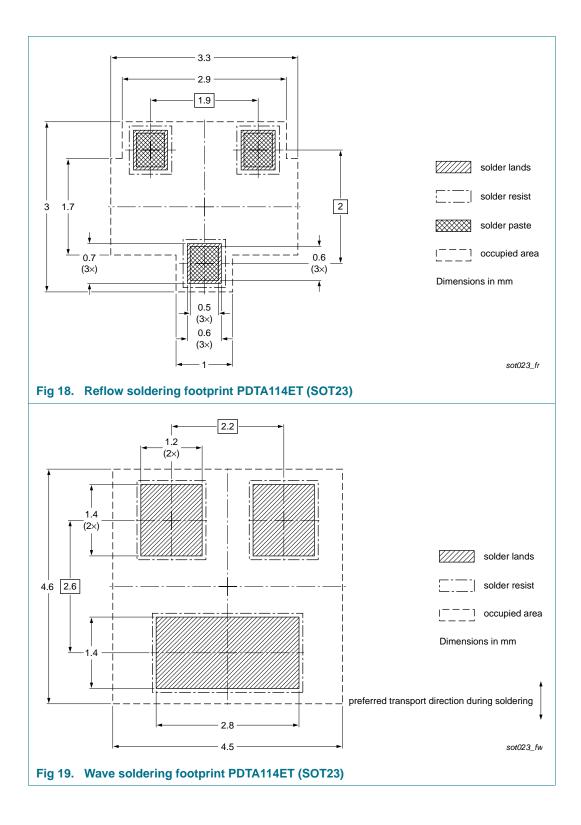
Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
PDTA114EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135		
PDTA114EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315		
PDTA114ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
PDTA114EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135		

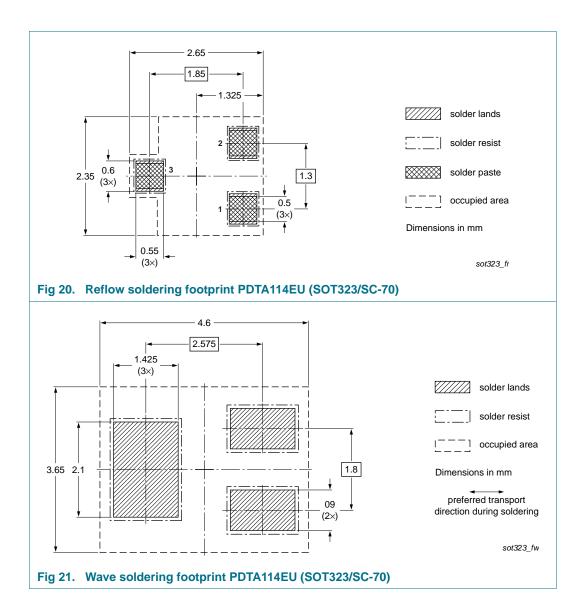
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

11. Soldering







PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

12. Revision history

Table 10. Revision histor	у			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA114E_SER v.10	20111221	Product data sheet	-	PDTA114E_SER v.9
Modifications:	 Figure 2 and 	d <u>5</u> : corrected		
PDTA114E_SER v.9	20111122	Product data sheet	-	PDTA114E_SERIES v.8
PDTA114E_SERIES v.8	20040802	Product specification	-	PDTA114E_SERIES v.7
PDTA114E_SERIES v.7	20030410	Product specification	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Product data sheet

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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